# 2SA1806

## Silicon PNP epitaxial planar type

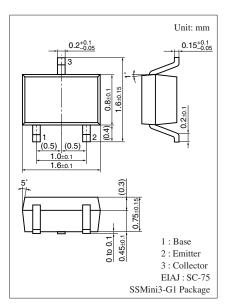
For high speed switching

#### Features

- High speed switching
- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- SS-Mini type package allowing downsizing of the equipment and automatic insertion through the tape packing

Parameter	Symbol	Rating	Unit			
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-15	V			
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-15	V			
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-4	V			
Collector current	I <sub>C</sub>	-50	mA			
Peak collector current	I <sub>CP</sub>	-100	mA			
Collector power dissipation	P <sub>C</sub>	125	mW			
Junction temperature	Tj	125	°C			
Storage temperature	T <sub>stg</sub>	-55 to +125	°C			

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$



#### Marking Symbol: AK

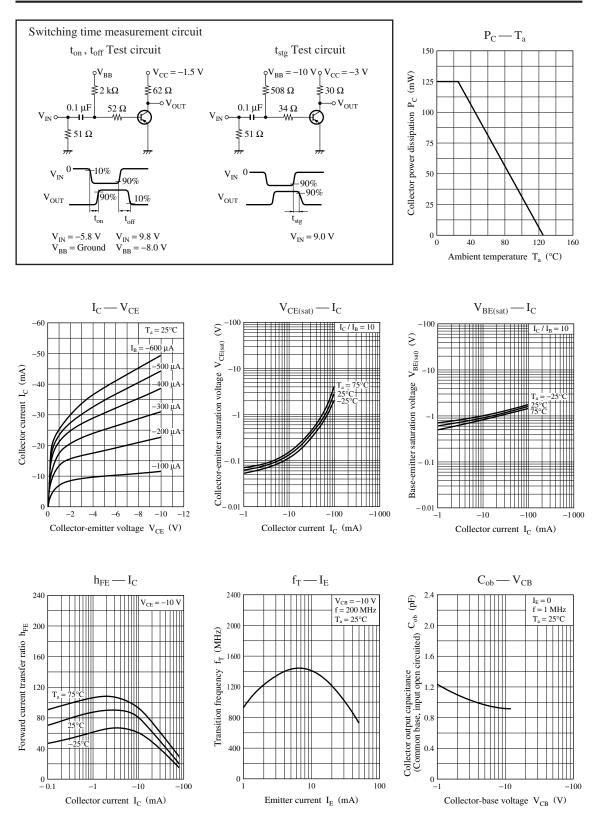
### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -8 V, I_E = 0$			- 0.1	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{CE} = -3 V, I_C = 0$			- 0.1	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -1 V, I_C = -10 mA$	50		150	
	h <sub>FE2</sub>	$V_{CE} = -1 V, I_C = -1 mA$	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}$		- 0.1	- 0.2	V
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$	800	1 500		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -5 V, I_E = 0, f = 1 MHz$		1		pF
Turn-on time	t <sub>on</sub>	Refer to the switching time measurement circuit		12		ns
Turn-off time	t <sub>off</sub>			20		ns
Storage time	t <sub>stg</sub>			19		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	Q	R
h <sub>FE1</sub>	50 to 120	90 to 150



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